



Docket No.: M4065.0959/P959
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Dean A. Klein

Application No.: 10/796,111

Confirmation No.: 2460

Filed: March 10, 2004

Art Unit: 2818

For: POWER MANAGEMENT CONTROL
AND CONTROLLING MEMORY
REFRESH OPERATIONS

Examiner: Not Yet Assigned

INFORMATION DISCLOSURE STATEMENT (IDS)

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Pursuant to 37 CFR 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached PTO/SB/08. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is filed within three months of the U.S. filing date (37 CFR 1.97(b)(1)).

Pursuant to United States Patent and Trademark Office Official Gazette Notice: 05 August 2003 ("Information Disclosure Statements May Be Filed Without Copies of U.S. Patents and Published Applications in Patent Applications filed after June 30, 2003") copies of the U.S. Patent Document references (i.e., references AA-AU7) on the PTO/SB/08 are not provided. Copies of the Foreign Patent Document references (i.e.,

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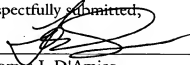
references BA, BB, and BC) and the Other Prior Art – Non Patent Literature Document References (i.e., references CA – CO6) on the PTO/SB/08 are provided.

In accordance with 37 CFR 1.97(g), the filing of this Information Disclosure Statement shall not be construed to mean that a search has been made or that no other material information as defined in 37 CFR 1.56(a) exists. In accordance with 37 CFR 1.97(h), the filing of this Information Disclosure statement shall not be construed to be an admission that any patent, publication or other information referred to therein is “prior art” for this invention unless specifically designated as such.

It is submitted that the Information Disclosure Statement is in compliance with 37 CFR 1.98 and the Examiner is respectfully requested to consider the listed references.

The Director is hereby authorized to charge any deficiency in the fees filed, asserted to be filed or which should have been filed herewith (or with any paper hereafter filed in this application by this firm) to our Deposit Account No. 04-1073, under Order No. M4065.0959/P959. A duplicate copy of this paper is enclosed.

Dated: June 10, 2004

Respectfully submitted,

By _____
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Approved for use through 10/31/2002. OMB 0551-0031
U. S. Patent and Trademark Office: U. S. DEPARTMENT OF COMMERCE
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Substitute for form 1449A/PTO			Complete if Known		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)			Application Number	10796,111	
			Filing Date	March 10, 2004	
			First Named Inventor	Dean A. Klein	
			Art Unit	2816 2824	
			Examiner Name	Not Yet Assigned	
Sheet	1	of	13	Attorney Docket Number	M4065.0959/P0959

U. S. PATENT DOCUMENTS					
Examiner Initials*	Cite No.	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code* (if known)			
/ML/		AA 2002/0000666	1/2002	Kozicki et al.	
		AB 2002/0072188	6/2002	Gilton	
		AC 2002/0106849	08/2002	Moore	
		AD 2002/0123169	09/2002	Moore et al.	
		AE 2002/0123170	09/2002	Moore et al.	
		AF 2002/0123248	09/2002	Moore et al.	
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		AH 2002/0132417	09/2002	Li	
		AI 2002/0160551	10/2002	Harshfield	
		AJ 2002/0163828	11/2002	Krieger et al.	
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		AN 2003/0027416	02/2003	Moore	
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		AP 2003/0038301	02/2003	Moore	
		AQ 2003/0043631	03/2003	Gilton et al.	
		AR 2003/0045049	03/2003	Campbell et al.	
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		AT 2003/0047765	03/2003	Campbell	
		AU 2003/0047772	03/2003	Li	
		AV 2003/0047773	03/2003	Li	
		AW 2003/0049912	03/2003	Campbell et al.	
		AX 2003/0068861	04/2003	Li	
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		AZ 2003/0095426	05/2003	Hush et al.	
		AA1 2003/0096497	05/2003	Moore et al.	
		AB1 2003/0107105	06/2003	Kozicki	
		AC1 2003/0117831	06/2003	Hush	
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		AF1 2003/0143782	07/2003	Gilton et al.	
		AG1 2003/0155589	08/2003	Campbell et al.	
		AH1 2003/0155606	08/2003	Campbell et al.	
		AI1 2003/0156447	08/2003	Kozicki	
		AJ1 2003/0156463	08/2003	Casper et al.	
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		AO1 3,743,847	7/1973	Boland	
		AP1 4,269,935	5/1981	Masters et al.	
		AQ1 4,312,938	1/1982	Drexler, et al.	
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				Filing Date	March 10, 2004
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				Art Unit	2010 2824
				Examiner Name	Not Yet Assigned
Sheet	2	of	13	Attorney Docket Number	M4065.0959/P0959

/ML/	AS1	4,320,191	3/1982	Yoshikawa et al.	
	AT1	4,405,710	9/1983	Balasubramanyam et al.	
	AU1	4,419,421	12/1983	Wichelhaus, et al.	
	AV1	4,499,557	2/1985	Holmberg et al.	
	AW1	4,671,618	06/1987	Wu et al.	
	AX1	4,795,657	1/1989	Formigoni et al.	
	AY1	4,800,526	01/1989	Lewis	
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	AA2	5,177,567	1/1993	Klersy et al.	
	AB2	5,219,788	6/1993	Abernathey et al.	
	AC2	5,238,862	8/1993	Bialock et al.	
	AD2	5,272,359	12/1993	Nagasubramanian et al.	
	AE2	5,314,772	5/1994	Kozicki	
	AF2	5,315,131	5/1994	Kishimoto et al.	
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	AH2	5,360,981	11/1994	Owen et al.	
	AI2	5,500,532	3/1996	Kozicki et al.	
	AJ2	5,512,328	4/1996	Yoshimura et al.	
	AK2	5,512,773	4/1996	Wolf et al.	
	AL2	5,726,083	3/1998	Takaishi	
	AM2	5,751,012	5/1998	Wolstenholme et al.	
	AN2	5,789,277	8/1998	Zahorik et al.	
	AO2	5,814,527	9/1998	Wolstenholme et al.	
	AP2	5,818,749	10/1998	Harshfield	
	AQ2	5,841,150	11/1998	Gonzalez et al.	
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	AS2	5,851,882	12/1998	Harshfield	
	AT2	5,869,843	2/1999	Harshfield	
	AU2	5,920,786	7/1999	Reinberg	
	AV2	5,998,066	12/1999	Block et al.	
	AW2	6,031,287	2/2000	Harshfield	
	AX2	6,072,716	6/2000	Jacobson et al.	
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	AA3	6,117,720	9/2000	Harshfield	
	AB3	6,143,604	11/2000	Chiang et al.	
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	AD3	6,297,170	10/2001	Gabriel et al.	
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	AH3	6,350,679	2/2002	McDaniel et al.	
	AI3	6,376,284	4/2002	Gonzalez et al.	
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Application Number	10/796,111
				Filing Date	March 10, 2004
				First Named Inventor	Dean A. Klein
				Art Unit	2040 2824
				Examiner Name	Not Yet Assigned
Sheet	3	of	13	Attorney Docket Number	M4065.0959/P0959

/ML/	AP3	6,440,837	8/2002	Harshfield	
	AQ3	6,469,364	10/2002	Kozicki	
	AR3	6,473,332	10/2002	Ignatiev et al.	
	AS3	US 2004/0035401	2/2004	Ramachandran et al.	
	AT3	US 2003/0212724	11/2003	Ovshinsky et al.	
	AU3	US 2003/0048744	3/2003	Ovshinsky et al.	
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	AX3	US 3,271,591	9/1966	Ovshinsky	
	AY3	US 3,961,314	6/1976	Klose et al.	
	AZ3	US 3,966,317	6/1976	Wacks et al.	
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	AC4	US 4,177,474	12/1979	Ovshinsky	
	AD4	US 4,267,261	5/1981	Hallman et al.	
	AE4	US 4,597,162	7/1986	Johnson et al.	
	AF4	US 4,608,296	8/1986	Keem et al.	
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	AV4	US 4,788,594	11/1988	Ovshinsky et al.	
	AW4	US 4,809,044	2/1989	Pryor et al.	
	AX4	US 4,818,717	4/1989	Johnson et al.	
	AY4	US 4,843,443	6/1989	Ovshinsky et al.	
	AZ4	US 4,845,533	7/1989	Pryor et al.	
	AA5	US 4,853,785	8/1989	Ovshinsky et al.	
	AB5	US 4,891,330	1/1990	Guha et al.	
	AC5	US 5,128,099	7/1992	Strand et al.	
	AD5	US 5,159,661	10/1992	Ovshinsky et al.	
	AE5	US 5,166,758	11/1992	Ovshinsky et al.	
	AF5	US 5,177,567	1/1993	Kiersy et al.	
	AG5	US 5,296,716	3/1994	Ovshinsky et al.	
	AH5	US 5,335,219	8/1994	Ovshinsky et al.	
	AI5	US 5,359,205	10/1994	Ovshinsky	
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PTO/SB/08A (10-01)

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>			Application Number	10796.111	
			Filing Date	March 10, 2004	
			First Named Inventor	Dean A. Klein	
			Art Unit	2818 2824	
			Examiner Name	Not Yet Assigned	
Sheet	4	of	13	Attorney Docket Number	M4065.0959/P0959

/ML/	AM5	US 5,534,711	7/1996	Ovshinsky et al.	
	AN5	US 5,534,712	7/1996	Ovshinsky et al.	
	AO5	US 5,536,947	7/1996	Kiersy et al.	
	AP5	US 5,543,737	8/1996	Ovshinsky	
	AQ5	US 5,591,501	1/1997	Ovshinsky et al.	
	AR5	US 5,596,522	1/1997	Ovshinsky et al.	
	AS5	US 5,687,112	11/1997	Ovshinsky	
	AT5	US 5,694,054	12/1997	Ovshinsky et al.	
	AU5	US 5,714,768	2/1998	Ovshinsky et al.	
	AV5	US 5,825,046	10/1998	Czubatyj et al.	
	AW5	US 5,912,839	6/1999	Ovshinsky et al.	
	AX5	US 5,933,365	8/1999	Kiersy et al.	
	AY5	US 6,011,757	1/2000	Ovshinsky	
	AZ5	US 6,087,674	7/2000	Ovshinsky et al.	
	AA6	US 6,141,241	10/2000	Ovshinsky et al.	
	AB6	US 6,339,544	1/2002	Chiang et al.	
	AC6	US 6,404,665	6/2002	Lowery et al.	
	AD6	US 6,429,064	8/2002	Wicker	
	AE6	US 6,437,383	8/2002	Xu	
	AF6	US 6,462,984	10/2002	Xu et al.	
	AG6	US 6,480,438	11/2002	Park	
	AH6	US 6,487,113	11/2002	Park et al.	
	AI6	US 6,501,111	12/2002	Lowery	
	AJ6	US 6,507,061	1/2003	Hudgens et al.	
	AK6	US 6,511,862	1/2003	Hudgens et al.	
	AL6	US 6,511,867	1/2003	Lowery et al.	
	AM6	US 6,512,241	1/2003	Lai	
	AN6	US 6,514,805	2/2003	Xu et al.	
	AO6	US 6,531,373	3/2003	Gill et al.	
	AP6	US 6,534,781	3/2003	Dennison	
	AQ6	US 6,545,287	4/2003	Chiang	
	AR6	US 6,545,907	4/2003	Lowery et al.	
	AS6	US 6,555,860	4/2003	Lowery et al.	
	AT6	US 6,563,164	5/2003	Lowery et al.	
	AU6	US 6,566,700	5/2003	Xu	
	AV6	US 6,567,293	5/2003	Lowery et al.	
	AW6	US 6,569,705	5/2003	Chiang et al.	
	AX6	US 6,570,784	5/2003	Lowery	
	AY6	US 6,576,921	6/2003	Lowery	
	AZ6	US 6,586,761	7/2003	Lowery	
	AA7	US 6,589,714	7/2003	Maimon et al.	
	AB7	US 6,590,807	7/2003	Lowery	
	AC7	US 6,593,176	7/2003	Dennison	
	AD7	US 6,597,009	7/2003	Wicker	
	AE7	US 6,605,527	8/2003	Dennison et al.	
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	AH7	US 6,625,054	9/2003	Lowery et al.	
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PTO/SB/08A (10-01)

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				Art Unit	2010 2824
				Examiner Name	Not Yet Assigned
Sheet	5	of	13	Attorney Docket Number	M4065.0959/P0959

/ML/	AJ7	US 6,646,297	11/2003	Dennison	
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	AJ7	US 6,667,900	12/2003	Lowery et al.	
	AM7	US 6,671,710	12/2003	Ovshinsky et al.	
	AN7	US 6,673,700	1/2004	Dennison et al.	
	AO7	US 6,674,115	1/2004	Huddens et al.	
	AP7	US 6,687,427	2/2004	Ramalingam et al.	
	AQ7	US 6,690,026	2/2004	Peterson	
	AR7	US 6,696,355	2/2004	Dennison	
✓	AS7	US 6,687,153	2/2004	Lowery	
/ML/	AT7	US 6,707,712	3/2004	Lowery	
/ML/	AU7	US 6,714,954	3/2004	Ovshinsky et al.	

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Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ²
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				
/ML/	BA	JP-56126916	10/1981	Akira et al.		
/ML/	BB	WO 97/48032	12/18/1997	Kozicki et al.		
/ML/	BC	WO 99/28914	06/10/1999	Kozicki et al.		
Examiner Signature /Pho Luu/			Date Considered		05/04/2009	

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PTO/SB/08B (10-01)

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	10/010,024 10/796-111
		Filing Date	July 14, 2003
		First Named Inventor	Terry L. Gilton
		Group Art Unit	7174 2824
		Examiner Name	Not Yet Assigned
Sheet	6	of	13
		Attorney Docket Number	M4065.1006/P1006-A

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
/ML/	CA	Abdel-Ail, A.; Eishafie, A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge ₂ As ₃ Te ₅ chalcogenide glass, <i>Vacuum</i> 59 (2000) 845-853.	
/ML/	CB	Adler, D.; Moss, S.C., Amorphous memories and bistable switches, <i>J. Vac. Sci. Technol.</i> 9 (1972) 1182-1189.	
/ML/	CC	Adler, D.; Henisch, H.K.; Mott, S.N., The mechanism of threshold switching in amorphous alloys, <i>Rev. Mod. Phys.</i> 50 (1978) 209-220.	
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/ML/	CE	Affifi, M.A.; Labib, H.H.; Fouad, S.S.; El-Shazly, A.A., Electrical & thermal conductivity of the amorphous semiconductor GexSe _{1-x} , <i>Egypt. J. Phys.</i> 17 (1986) 335-342.	
/ML/	CF	Alekperova, Sh.M.; Gadzhieva, G.S., Current-Voltage characteristics of Ag ₂ Se single crystal near the phase transition, <i>Inorganic Materials</i> 23 (1987) 137-139.	
/ML/	CG	Aleksiejunas, A.; Cesnys, A., Switching phenomenon and memory effect in thin-film heterojunction of polycrystalline selenium-silver selenide, <i>Phys. Stat. Sol. (a)</i> 19 (1973) K169-K171.	
/ML/	CH	Angeli, C.A., Mobile ions in amorphous solids, <i>Annu. Rev. Phys. Chem.</i> 43 (1992) 693-717.	
/ML/	CI	Aniya, M., Average electronegativity, medium-range-order, and ionic conductivity in superionic glasses, <i>Solid state Ionics</i> 136-137 (2000) 1085-1089.	
/ML/	CJ	Asahara, Y.; Izumitani, T., Voltage controlled switching in Cu-As-Se compositions, <i>J. Non-Cryst. Solids</i> 11 (1972) 97-104.	
/ML/	CK	Asokan, S.; Prasad, M.V.N.; Parthasarathy, G.; Gopal, E.S.R., Mechanical and chemical thresholds in IV-VI chalcogenide glasses, <i>Phys. Rev. Lett.</i> 62 (1989) 808-810.	
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Sheet 11 of 13

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Substitute for form 1449B/PTO <h2 style="text-align: center;">INFORMATION DISCLOSURE STATEMENT BY APPLICANT</h2> <p style="text-align: center;">(use as many sheets as necessary)</p>				Complete if Known Application Number <u>10/648,824</u> <u>10/796-111</u> Filing Date <u>July 14, 2003</u> First Named Inventor <u>Terry L. Gilton</u> Group Art Unit <u>N/A</u> <u>2824</u> Examiner Name <u>Not Yet Assigned</u> Attorney Docket Number <u>M4065.1006/P1006-A</u>	
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